

IN THE ABSTRACT

Please replace the abstract of the disclosure at page 14 of the application with the following:

ABSTRACT

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An epitaxial growth furnace is provided for effecting the formation of an epitaxial layer on the surface of a semiconductor wafer by CVD in a reaction chamber of the furnace. The furnace comprises a wafer holder having an opening for exposing a surface area of the wafer which is subject to epitaxial growth, an opening flange adapted for engagement with a chamfered tapered face of a whole peripheral edge of the wafer on the side of said surface area thereof, and a plurality of jaws for detachably engaging with an outer periphery of the wafer on a back surface side of said surface area.
